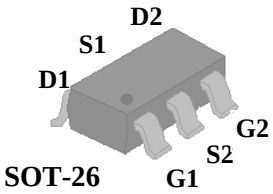
AP2532GY

RoHS-compliant Product

Advanced Power Electronics Corp.

N AND P-CHANNEL ENHANCEMENT MODE POWER MOSFET

- ▼ **Low Gate Charge**
- ▼ **Fast Switching Performance**
- ▼ **Surface Mount Package**

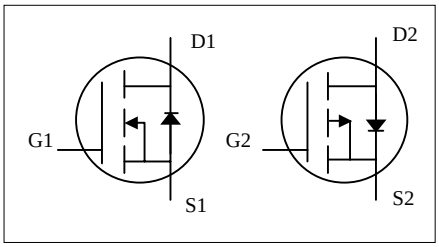


N-CH	BV_{DSS}	30V
	$R_{DS(ON)}$	130mΩ
	I_D	2.4A
P-CH	BV_{DSS}	-30V
	$R_{DS(ON)}$	250mΩ
	I_D	-1.8A

Description

Advanced Power MOSFETs utilized advanced processing techniques to achieve the lowest possible on-resistance, extremely efficient and cost-effectiveness device.

The SOT-26 package is widely used for commercial surface mount applications.



Absolute Maximum Ratings

Symbol	Parameter	Rating		Units
		N-channel	P-channel	
V_{DS}	Drain-Source Voltage	30	-30	V
V_{GS}	Gate-Source Voltage	±20	±20	V
I_D@T_A=25℃	Continuous Drain Current[3]	2.4	-1.8	A
I_D@T_A=70℃	Continuous Drain Current[3]	1.9	-1.4	A
I_{DM}	Pulsed Drain Current[1]	10	-10	A
P_D@T_A=25℃	Total Power Dissipation	1.14		W
	Linear Derating Factor	0.01		W/℃
T_{STG}	Storage Temperature Range	-55 to 150		℃
T_J	Operating Junction Temperature Range	-55 to 150		℃

Thermal Data

Symbol	Parameter	Value	Unit
Rthj-a	Maximum Thermal Resistance, Junction-ambient[3]	110	℃/W

N-CH Electrical Characteristics@T_j=25°C(unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V, I_D=250uA	30	-	-	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance[2]	V_{GS}=10V, I_D=1A	-	-	130	mΩ
		V_{GS}=4.5V, I_D=0.5A	-	-	250	mΩ
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_D=250uA	1.2	-	3	V
g_{fs}	Forward Transconductance	V_{DS}=10V, I_D=1A	-	1.6	-	S
I_{DSS}	Drain-Source Leakage Current (T_j=25°C)	V_{DS}=30V, V_{GS}=0V	-	-	1	uA
	Drain-Source Leakage Current (T_j=70°C)	V_{DS}=24V, V_{GS}=0V	-	-	25	uA
I_{GSS}	Gate-Source Leakage	V_{GS}=±20V	-	-	±100	nA
Q_g	Total Gate Charge[2]	I_D=1.8A	-	2.7	4.3	nC
Q_{gs}	Gate-Source Charge	V_{DS}=10V	-	0.9	-	nC
Q_{gd}	Gate-Drain ("Miller") Charge	V_{GS}=4.5V	-	1.2	-	nC
$t_{d(on)}$	Turn-on Delay Time[2]	V_{DS}=15V	-	4.3	-	ns
t_r	Rise Time	I_D=1A	-	10	-	ns
$t_{d(off)}$	Turn-off Delay Time	R_G=3.3Ω,V_{GS}=10V	-	12	-	ns
t_f	Fall Time	R_D=15Ω	-	2.5	-	ns
C_{iss}	Input Capacitance	V_{GS}=0V	-	180	290	pF
C_{oss}	Output Capacitance	V_{DS}=10V	-	70	-	pF
C_{rss}	Reverse Transfer Capacitance	f=1.0MHz	-	50	-	pF
R_g	Gate Resistance	f=1.0MHz	-	1.7	2.6	Ω

Source-Drain Diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
V_{SD}	Forward On Voltage[2]	I_S=0.9A, V_{GS}=0V	-	-	1.3	V
t_{rr}	Reverse Recovery Time	I_S=1.8A, V_{GS}=0V	-	16	-	ns
Q_{rr}	Reverse Recovery Charge	dI/dt=100A/μs	-	10	-	nC

P-CH Electrical Characteristics@T_j=25°C(unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V, I_D=-250uA	-30	-	-	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS}=-10V, I_D=-0.6A	-	-	250	mΩ
		V_{GS}=-4.5V, I_D=-0.3A	-	-	400	mΩ
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_D=-250uA	-1.2	-	-3	V
g_{fs}	Forward Transconductance	V_{DS}=-10V, I_D=-1A	-	1.7	-	S
I_{DSS}	Drain-Source Leakage Current (T_j=25°C)	V_{DS}=-30V, V_{GS}=0V	-	-	-1	uA
	Drain-Source Leakage Current (T_j=70°C)	V_{DS}=-24V ,V_{GS}=0V	-	-	-25	uA
I_{GSS}	Gate-Source Leakage	V_{GS}=±20V	-	-	±100	nA
Q_g	Total Gate Charge[2]	I_D=-1.2A	-	2.5	4	nC
Q_{gs}	Gate-Source Charge	V_{DS}=-10V	-	1	-	nC
Q_{gd}	Gate-Drain ("Miller") Charge	V_{GS}=-4.5V	-	1	-	nC
$t_{d(on)}$	Turn-on Delay Time[2]	V_{DS}=-15V	-	6	-	ns
t_r	Rise Time	I_D=-0.6A	-	9	-	ns
$t_{d(off)}$	Turn-off Delay Time	R_G=3.3Ω,V_{GS}=-10V	-	18	-	ns
t_f	Fall Time	R_D=25Ω	-	4	-	ns
C_{iss}	Input Capacitance	V_{GS}=0V	-	175	280	pF
C_{oss}	Output Capacitance	V_{DS}=-10V	-	63	-	pF
C_{rss}	Reverse Transfer Capacitance	f=1.0MHz	-	45	-	pF
R_g	Gate Resistance	f=1.0MHz	-	10	15	Ω

Source-Drain Diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V_{SD}	Forward On Voltage[2]	I_S=-0.9A, V_{GS}=0V	-	-	-1.3	V
t_{rr}	Reverse Recovery Time	I_S=-1.2A, V_{GS}=0V,	-	14	-	ns
Q_{rr}	Reverse Recovery Charge	dI/dt=100A/μs	-	6	-	nC

Notes:

1.Pulse width limited by Max. junction temperature.

2.Pulse test

3.Surface mounted on 1 in^2 copper pad of FR4 board, t≤5sec ; 180℃/W when mounted on min. copper pad.

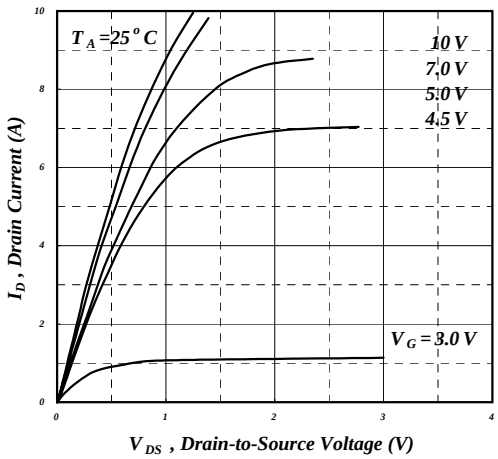


Fig 1. Typical Output Characteristics

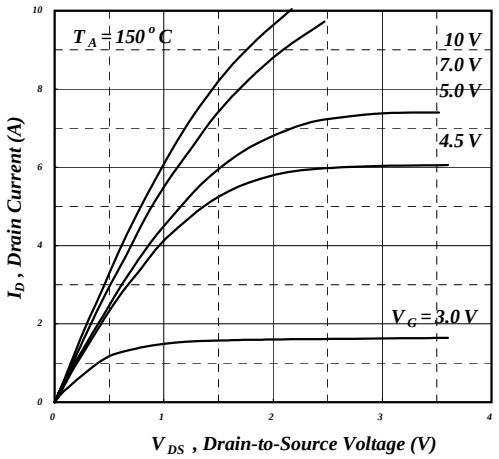


Fig 2. Typical Output Characteristics

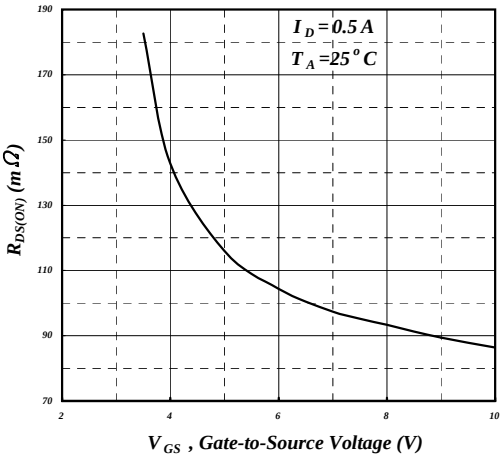


Fig 3. On-Resistance v.s. Gate Voltage

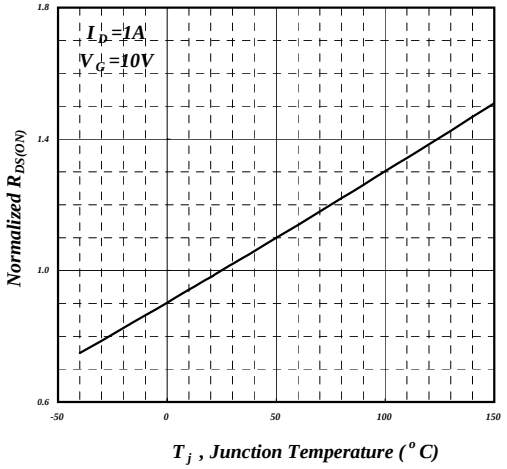


Fig 4. Normalized On-Resistance v.s. Junction Temperature

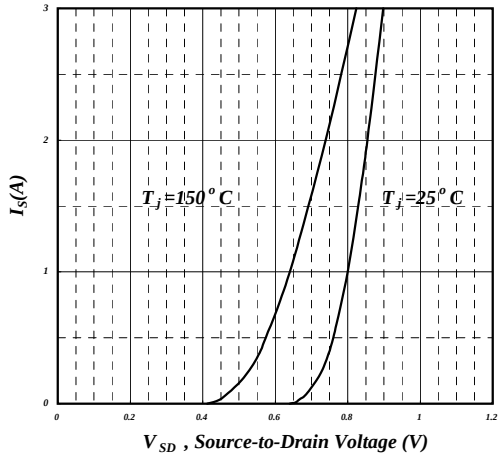


Fig 5. Forward Characteristic of Reverse Diode

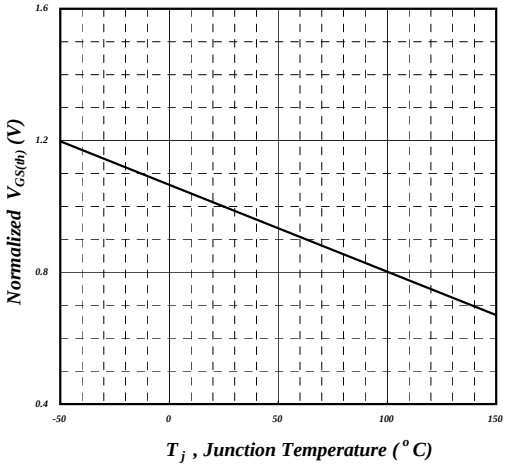


Fig 6. Gate Threshold Voltage v.s. Junction Temperature

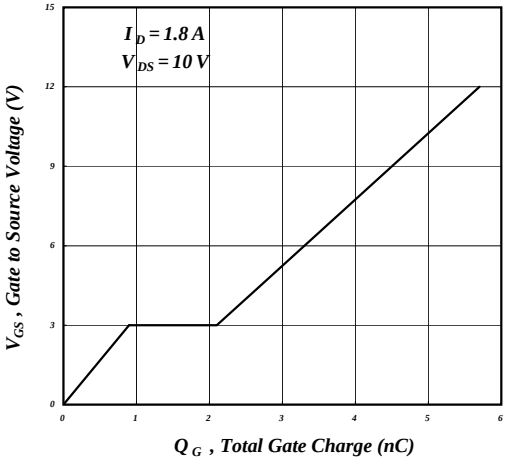


Fig 7. Gate Charge Characteristics

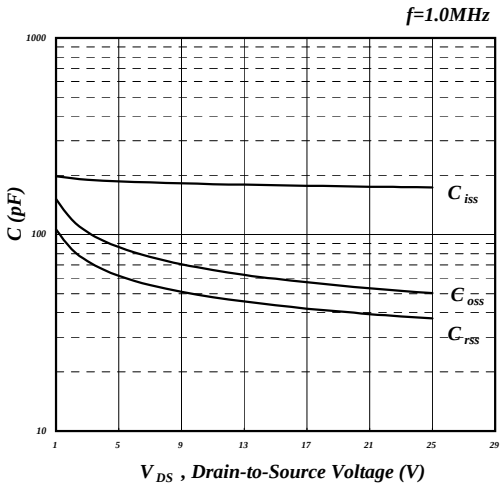


Fig 8. Typical Capacitance Characteristics

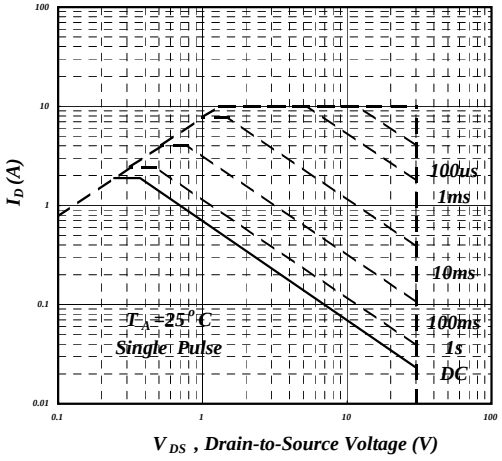


Fig 9. Maximum Safe Operating Area

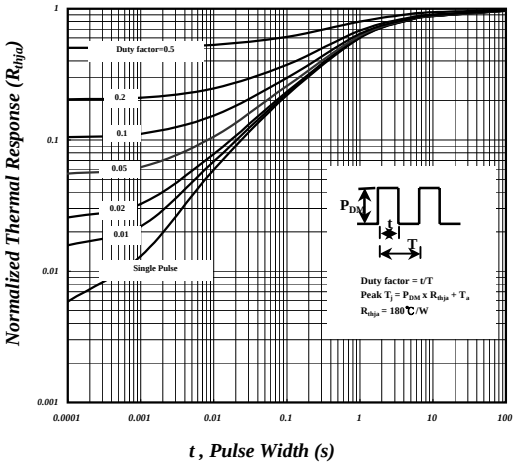


Fig 10. Effective Transient Thermal Impedance

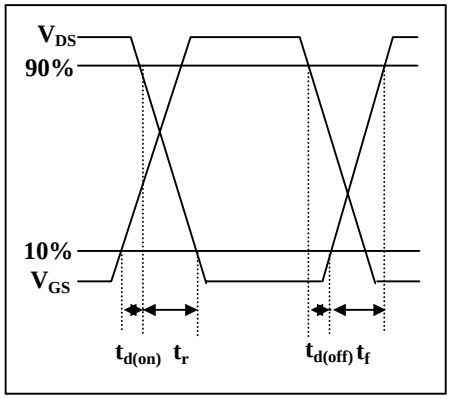


Fig 11. Switching Time Waveform

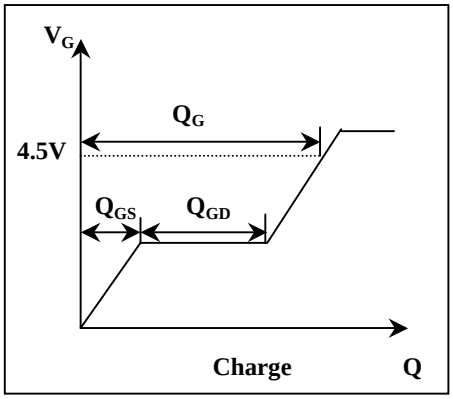


Fig 12. Gate Charge Waveform

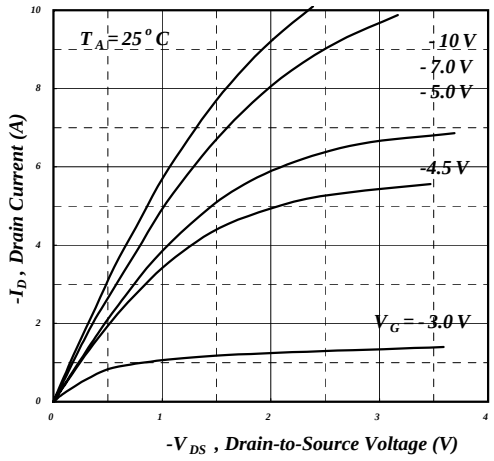


Fig 1. Typical Output Characteristics

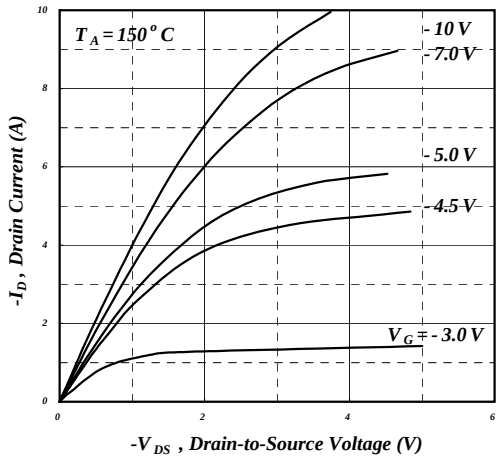


Fig 2. Typical Output Characteristics

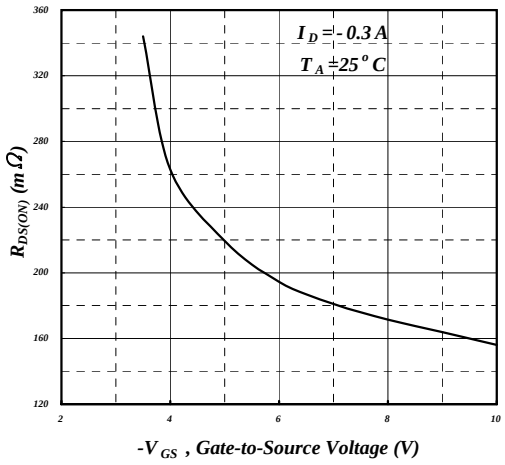


Fig 3. On-Resistance v.s. Gate Voltage

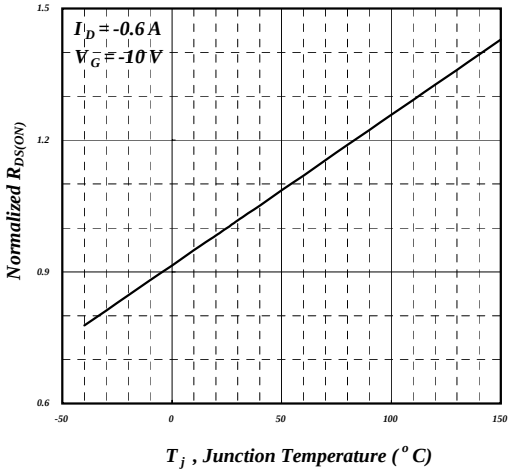


Fig 4. Normalized On-Resistance v.s. Junction Temperature

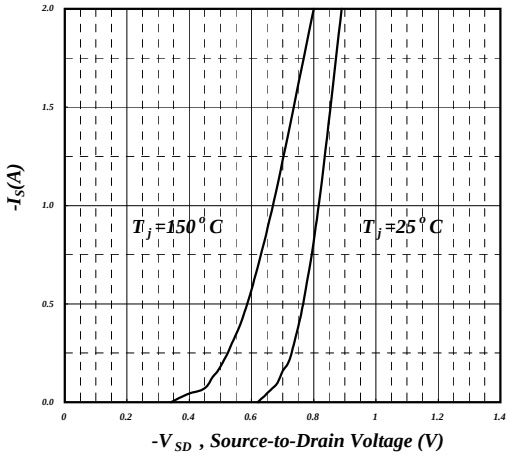


Fig 5. Forward Characteristic of Reverse Diode

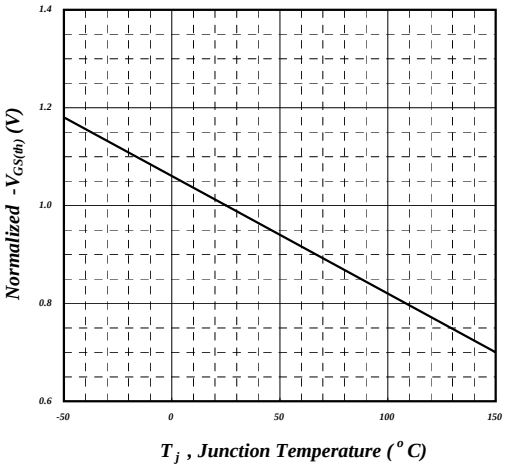


Fig 6. Gate Threshold Voltage v.s. Junction Temperature

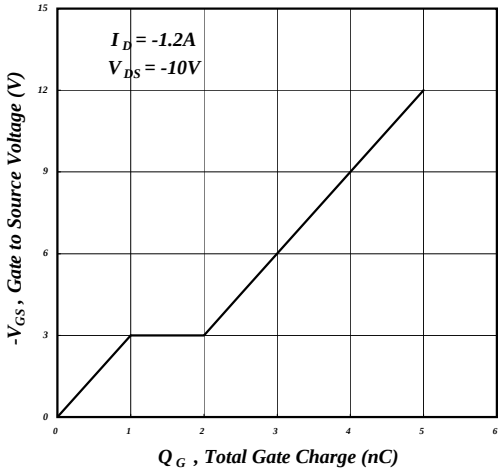
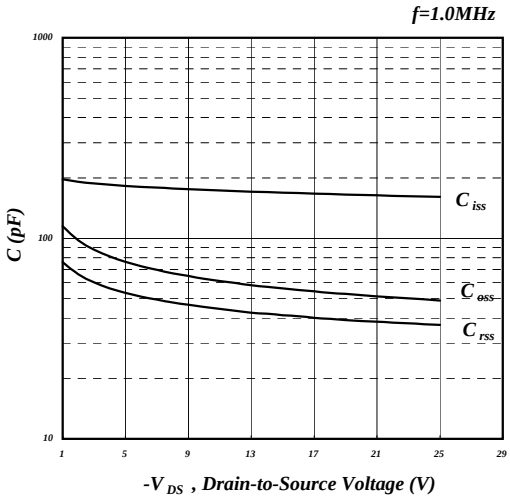


Fig 7. Gate Charge Characteristics



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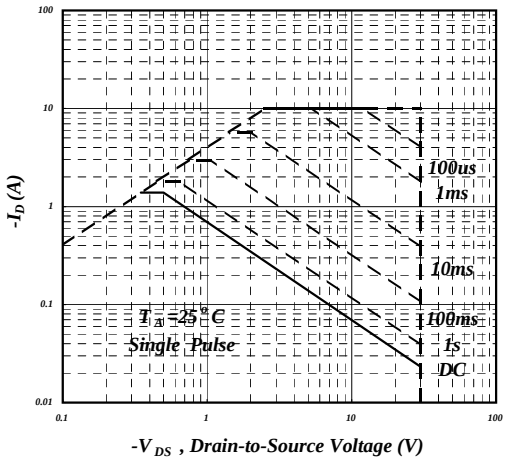


Fig 9. Maximum Safe Operating Area

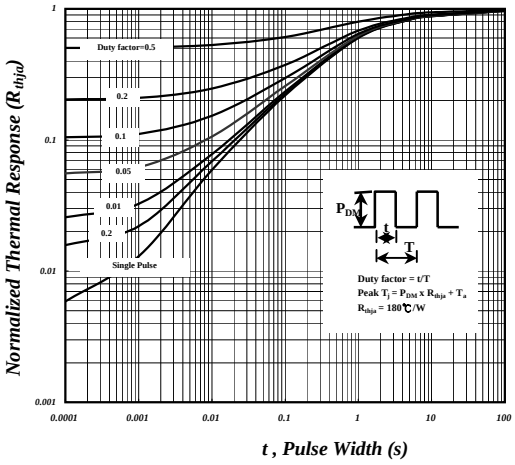


Fig 10. Effective Transient Thermal Impedance

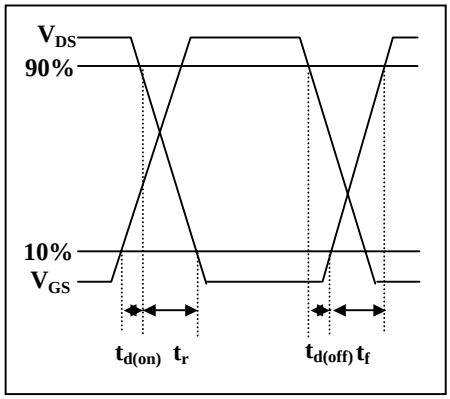


Fig 11. Switching Time Waveform

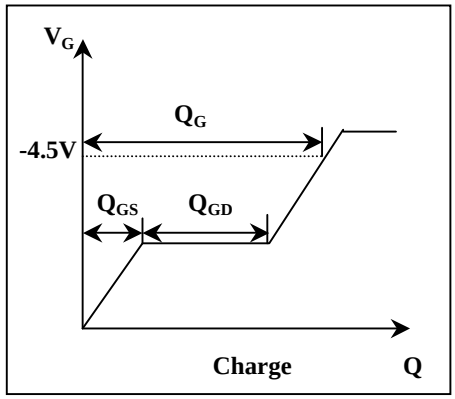
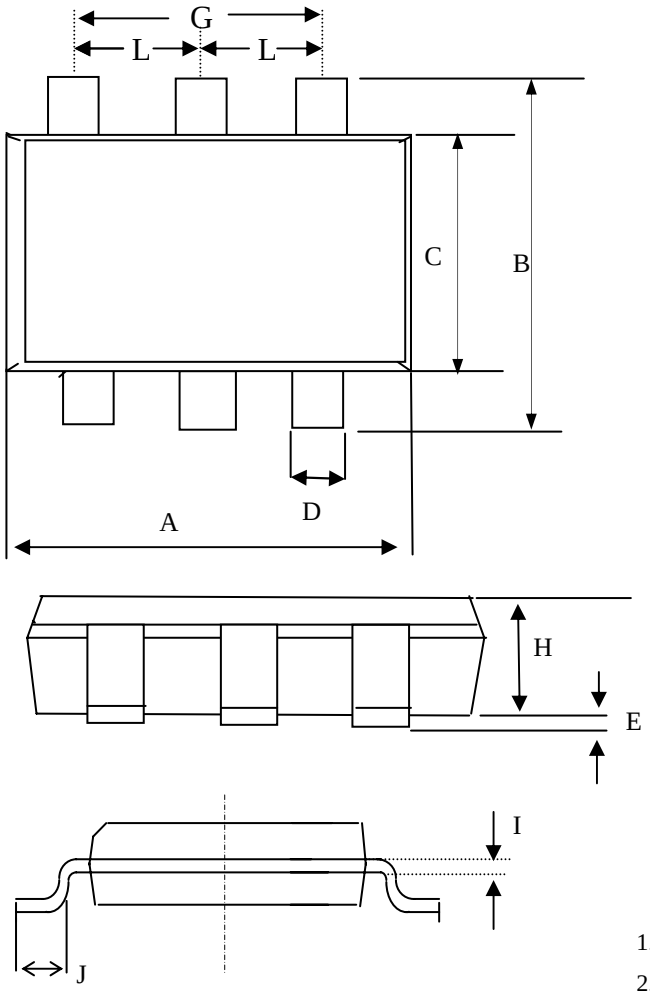


Fig 12. Gate Charge Waveform

Package Outline : SOT-26



SYMBOLS	Millimeters		
	MIN	NOM	MAX
A	2.70	2.90	3.10
B	2.60	2.80	3.00
C	1.40	1.60	1.80
D	0.30	0.43	0.55
E	0.00	0.05	0.10
H	1.20REF		
G	1.90REF		
I	0.12REF		
J	0.37REF		
L	0.95REF		

1.All Dimension Are In Millimeters.

2.Dimension Does Not Include Mold Protrusions.

Part Marking Information & Packing : SOT-26